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Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications.

Details

Product Status	Active
Number of LABs/CLBs	960
Number of Logic Elements/Cells	7680
Total RAM Bits	131072
Number of I/O	206
Number of Gates	-
Voltage - Supply	1.14V ~ 1.26V
Mounting Type	Surface Mount
Operating Temperature	-40°C ~ 100°C (TJ)
Package / Case	256-LFBGA
Supplier Device Package	256-CABGA (14x14)
Purchase URL	https://www.e-xfl.com/product-detail/lattice-semiconductor/ice40hx8k-ct256

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iCE40 LP/HX Family Data Sheet Architecture

March 2017

Data Sheet DS1040

Architecture Overview

The iCE40 family architecture contains an array of Programmable Logic Blocks (PLB), sysCLOCK[™] PLLs, Nonvolatile Programmable Configuration Memory (NVCM) and blocks of sysMEM[™] Embedded Block RAM (EBR) surrounded by Programmable I/O (PIO). Figure 2-1 shows the block diagram of the iCE40LP/HX1K device.

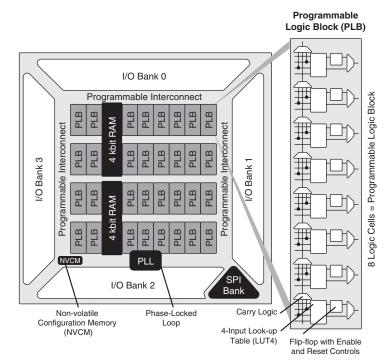


Figure 2-1. iCE40LP/HX1K Device, Top View

The logic blocks, Programmable Logic Blocks (PLB) and sysMEM EBR blocks, are arranged in a two-dimensional grid with rows and columns. Each column has either logic blocks or EBR blocks. The PIO cells are located at the periphery of the device, arranged in banks. The PLB contains the building blocks for logic, arithmetic, and register functions. The PIOs utilize a flexible I/O buffer referred to as a sysIO buffer that supports operation with a variety of interface standards. The blocks are connected with many vertical and horizontal routing channel resources. The place and route software tool automatically allocates these routing resources.

In the iCE40 family, there are up to four independent sysIO banks. Note on some packages V_{CCIO} banks are tied together. There are different types of I/O buffers on the different banks. Refer to the details in later sections of this document. The sysMEM EBRs are large 4 kbit, dedicated fast memory blocks. These blocks can be configured as RAM, ROM or FIFO.

The iCE40 architecture also provides up to two sysCLOCK Phase Locked Loop (PLL) blocks. The PLLs have multiply, divide, and phase shifting capabilities that are used to manage the frequency and phase relationships of the clocks.

Every device in the family has a SPI port that supports programming and configuration of the device. The iCE40 includes on-chip, Nonvolatile Configuration Memory (NVCM).

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Routing

There are many resources provided in the iCE40 devices to route signals individually with related control signals. The routing resources consist of switching circuitry, buffers and metal interconnect (routing) segments.

The inter-PLB connections are made with three different types of routing resources: Adjacent (spans two PLBs), x4 (spans five PLBs) and x12 (spans thirteen PLBs). The Adjacent, x4 and x12 connections provide fast and efficient connections in the diagonal, horizontal and vertical directions.

The design tool takes the output of the synthesis tool and places and routes the design.

Clock/Control Distribution Network

Each iCE40 device has eight global inputs, two pins on each side of the device. Note that not all GBINs are available in all packages.

These global inputs can be used as high fanout nets, clock, reset or enable signals. The dedicated global pins are identified as GBIN[7:0] and the global buffers are identified as-GBUF[7:0]. These eight inputs may be used as general purpose I/O if they are not used to drive the clock nets. Global buffer GBUF7 in I/O Bank 3 also provides an optional direct LVDS25 or subLVDS differential clock input.

Table 2-2 lists the connections between a specific global buffer and the inputs on a PLB. All global buffers optionally connect to the PLB CLK input. Any four of the eight global buffers can drive logic inputs to a PLB. Even-numbered global buffers optionally drive the Set/Reset input to a PLB. Similarly, odd-numbered buffers optionally drive the PLB clock-enable input.

Global Buffer	LUT Inputs	Clock	Reset	Clock Enable
GBUF0		Yes	Yes	
GBUF1		Yes		Yes
GBUF2	7	Yes	Yes	
GBUF3	Yes, any 4 of 8	Yes		Yes
GBUF4	GBUF Inputs	Yes	Yes	
GBUF5		Yes		Yes
GBUF6		Yes	Yes	
GBUF7		Yes		Yes

Table 2-2. Global Buffer (GBUF) Connections to Programmable Logic Blocks

The maximum frequency for the global buffers are shown in the iCE40 External Switching Characteristics tables later in this document.

Global Hi-Z Control

The global high-impedance control signal, GHIZ, connects to all I/O pins on the iCE40 device. This GHIZ signal is automatically asserted throughout the configuration process, forcing all user I/O pins into their high-impedance state.



RAM Initialization and ROM Operation

If desired, the contents of the RAM can be pre-loaded during device configuration.

By preloading the RAM block during the chip configuration cycle and disabling the write controls, the sysMEM block can also be utilized as a ROM.

Note the sysMEM Embedded Block RAM Memory address 0 cannot be initialized.

Memory Cascading

Larger and deeper blocks of RAM can be created using multiple EBR sysMEM Blocks.

RAM4k Block

Figure 2-4 shows the 256x16 memory configurations and their input/output names. In all the sysMEM RAM modes, the input data and addresses for the ports are registered at the input of the memory array.

Figure 2-4. sysMEM Memory Primitives

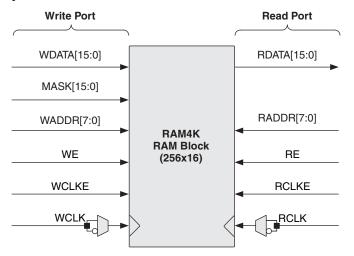


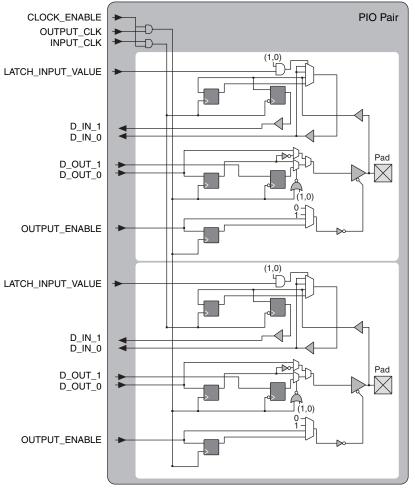
Table 2-5. EBR Signal Descriptions

Signal Name	Direction	Description
WDATA[15:0]	Input	Write Data input.
MASK[15:0]	Input	Masks write operations for individual data bit-lines. 0 = write bit; 1 = don't write bit
WADDR[7:0]	Input	Write Address input. Selects one of 256 possible RAM locations.
WE	Input	Write Enable input.
WCLKE	Input	Write Clock Enable input.
WCLK	Input	Write Clock input. Default rising-edge, but with falling-edge option.
RDATA[15:0]	Output	Read Data output.
RADDR[7:0]	Input	Read Address input. Selects one of 256 possible RAM locations.
RE	Input	Read Enable input.
RCLKE	Input	Read Clock Enable input.
RCLK	Input	Read Clock input. Default rising-edge, but with falling-edge option.

For further information on the sysMEM EBR block, please refer to TN1250, Memory Usage Guide for iCE40 Devices.



Figure 2-6. iCE I/O Register Block Diagram



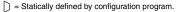


Table 2-6. PIO Signal List

Pin Name	I/O Type Description	
OUTPUT_CLK	Input	Output register clock
CLOCK_ENABLE	Input	Clock enable
INPUT_CLK	Input	Input register clock
OUTPUT_ENABLE	Input	Output enable
D_OUT_0/1	Input	Data from the core
D_IN_0/1	Output	Data to the core
LATCH_INPUT_VALUE	Input	Latches/holds the Input Value

sysIO Buffer

Each I/O is associated with a flexible buffer referred to as a sysIO buffer. These buffers are arranged around the periphery of the device in groups referred to as banks. The sysIO buffers allow users to implement a wide variety of standards that are found in today's systems including LVCMOS and LVDS25.

High Current LED Drivers combine three sysIO buffers together. This allows for programmable drive strength. This also allows for high current drivers that are ideal to drive three white LEDs, or one RGB LED. Each bank is capable of supporting multiple I/O standards including single-ended LVCMOS buffers and differential LVDS25E output buf-



Power On Reset

iCE40 devices have power-on reset circuitry to monitor V_{CC} , V_{CCIO_2} , V_{PP_2V5} , and V_{CC_SPI} voltage levels during power-up and operation. At power-up, the POR circuitry monitors V_{CC} , V_{CCIO_2} , V_{PP_2V5} , and V_{CC_SPI} (controls configuration) voltage levels. It then triggers download from the on-chip NVCM or external Flash memory after reaching the power-up levels specified in the Power-On-Reset Voltage table in the DC and Switching Characteristics section of this data sheet. Before and during configuration, the I/Os are held in tri-state. I/Os are released to user functionality once the device has finished configuration.

Programming and Configuration

This section describes the programming and configuration of the iCE40 family.

Device Programming

The NVCM memory can be programmed through the SPI port.

Device Configuration

There are various ways to configure the Configuration RAM (CRAM) including:

- 1. Internal NVCM Download
- 2. From a SPI Flash (Master SPI mode)
- 3. System microprocessor to drive a Serial Slave SPI port (SSPI mode)

The image to configure the CRAM can be selected by the user on power up (Cold Boot) or once powered up (Warm Boot).

For more details on programming and configuration, see TN1248, iCE40 Programming and Configuration Usage Guide.

Power Saving Options

iCE40 devices are available in two options for maximum flexibility: LP and HX devices. The LP devices have ultra low static and dynamic power consumption. HX devices are designed to provide high performance. Both the LP and the HX devices operate at 1.2 V V_{CC} .

iCE40 devices feature iCEGate and PLL low power mode to allow users to meet the static and dynamic power requirements of their applications. While these features are available in both device types, these features are mainly intended for use with iCE40 LP devices to manage power consumption.

Table 2-9. iCE40 Power Saving Features Description

Device Subsystem	Feature Description
	When LATCHINPUTVALUE is enabled, forces the PLL into low-power mode; PLL output held static at last input clock value.
	To save power, the optional iCEgate latch can selectively freeze the state of individual, non-regis- tered inputs within an I/O bank. Registered inputs are effectively frozen by their associated clock or clock-enable control.



iCE40 LP/HX Family Data Sheet DC and Switching Characteristics

October 2015

Data Sheet DS1040

Absolute Maximum Ratings^{1, 2, 3, 4}

iCE40 LP/HX

Supply Voltage V _{CC}	/
Output Supply Voltage V _{CCIO} , V _{CC_SPI} 0.5 V to 3.60 V	/
NVCM Supply Voltage V _{PP_2V5}	/
PLL Supply Voltage V _{CCPLL} 0.5 V to 1.30 V	/
I/O Tri-state Voltage Applied	/
Dedicated Input Voltage Applied0.5 V to 3.60 V	/
Storage Temperature (Ambient)65 °C to 150 °C	С
Junction Temperature (T _J)55 °C to 125 °C	С

1. Stress above those listed under the "Absolute Maximum Ratings" may cause permanent damage to the device. Functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied.

2. Compliance with the Lattice Thermal Management document is required.

3. All voltages referenced to GND.

 IOs can support a 200 mV Overshoot above the Recommend Operating Conditions V_{CCIO} (Max) and -200mV Undershoot below V_{IL} (Min). Overshoot and Undershoot is permitted for 25% duty cycle but must not exceed 1.6 ns.

Recommended Operating Conditions¹

Symbol	Param	neter	Min.	Max.	Units
V _{CC} ¹	Core Supply Voltage		1.14	1.26	V
		Slave SPI Configuration	1.71	3.46	V
V	V _{PP_2V5} NVCM Programming and Operating Supply Voltage	Master SPI Configuration	2.30	3.46	V
V _{PP_2V5}	Operating Supply Voltage	Configure from NVCM	2.30	3.46	V
		NVCM Programming	2.30	3.00	V
V _{PP_FAST} ⁴	Optional fast NVCM programming supply. Leave unconnected.		N/A	N/A	V
V _{CCPLL} ^{5, 6}	PLL Supply Voltage	PLL Supply Voltage		1.26	V
V _{CCIO} ^{1, 2, 3}	I/O Driver Supply Voltage	V _{CCIO0-3}	1.71	3.46	V
V CCIO	NO Driver Supply Voltage	V _{CC_SPI}	1.71	3.46	V
t _{JIND}	Junction Temperature Industrial Operation		-40	100	°C
t _{PROG}	Junction Temperature NVCM Programm	ing	10	30	°C

1. Like power supplies must be tied together. For example, if V_{CCIO} and V_{CC_SPI} are both the same voltage, they must also be the same supply.

2. See recommended voltages by I/O standard in subsequent table.

3. V_{CCIO} pins of unused I/O banks should be connected to the V_{CC} power supply on boards.

V_{PP_FAST}, used only for fast production programming, must be left floating or unconnected in applications, except CM36 and CM49 packages MUST have the V_{PP_FAST} ball connected to V_{CCIO_0} ball externally.

5. No PLL available on the iCE40LP384 and iCE40LP640 device.

6. V_{CCPLL} is tied to V_{CC} internally in packages without PLLs pins.

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Power Supply Ramp Rates^{1, 2}

Symbol	Parameter		Min.	Max.	Units
		All configuration modes. No power supply sequencing.	0.40	10	V/ms
		Configuring from Slave SPI. No power supply sequencing,	0.01	10	V/ms
t _{RAMP}	Power supply ramp rates for all power supplies.	Configuring from NVCM. V_{CC} and $V_{PP_{2V5}}$ to be powered 0.25 ms before $V_{CC_{SPI}}$.	0.01	10	V/ms
		Configuring from MSPI. V_{CC} and V_{PP_SPI} to be powered 0.25 ms before V_{PP_2V5} .	0.01	10	V/ms

1. Assumes monotonic ramp rates.

2. iCE40LP384 requires V_{CC} to be greater than 0.7V when V_{CCIO} and V_{CC_SPI} are above GND.

Power-On-Reset Voltage Levels¹

Symbol	Device	Parameter		Min.	Max.	Units
V _{PORUP}	iCE40LP384	Power-On-Reset ramp-up trip point	VCC	0.67	0.99	V
		(band gap based circuit monitoring VCC, VCCIO_2, VCC_SPI and	VCCIO_2	0.70	1.59	V
		VPP_2V5)	VCC_SPI	0.70	1.59	V
			VPP_2V5	0.70	1.59	V
	iCE40LP640,	Power-On-Reset ramp-up trip point	VCC	0.55	0.75	V
	iCE40LP/HX1K, iCE40LP/HX4K,	(band gap based circuit monitoring VCC, VCCIO_2, VCC_SPI and	VCCIO_2	0.86	1.29	V
	iCE40LP/HX8K	VPP_2V5)	VCC_SPI	0.86	1.29	V
			VPP_2V5	0.86	1.33	V
V _{PORDN}	/ _{PORDN} iCE40LP384	Power-On-Reset ramp-down trip	VCC	—	0.64	V
		point (band gap based circuit moni- toring VCC, VCCIO_2, VCC_SPI	VCCIO_2	—	1.59	V
		and VPP_2V5)	VCC_SPI	—	1.59	V
			VPP_2V5	—	1.59	V
	iCE40LP640,	Power-On-Reset ramp-down trip	VCC	—	0.75	V
	iCE40LP/HX1K, iCE40LP/HX4K,	point (band gap based circuit moni- toring VCC, VCCIO_2, VCC_SPI and VPP 2V5)	VCCIO_2	—	1.29	V
			VCC_SPI	—	1.29	V
			VPP_2V5	—	1.33	V

1. These POR trip points are only provided for guidance. Device operation is only characterized for power supply voltages specified under recommended operating conditions.

ESD Performance

Please refer to the iCE40 Product Family Qualification Summary for complete qualification data, including ESD performance.



Programming NVCM Supply Current – HX Devices^{1, 2, 3, 4}

Symbol	Parameter	Device	Typ. V _{CC} ⁵	Units
		iCE40HX1K	278	μΑ
I _{CC}	Core Power Supply	iCE40HX4K	1174	μΑ
		iCE40HX8K	1174	μΑ
I _{CCPLL} ⁶	PLL Power Supply	All devices	0.5	μA
I _{PP_2V5}	NVCM Power Supply	All devices	2.5	mA
I _{CCIO⁷, I_{CC_SPI}}	Bank Power Supply⁵	All devices	3.5	mA

1. Assumes all inputs are held at V_{CCIO} or GND and all outputs are tri-stated.

2. Typical user pattern.

3. SPI programming is at 8 MHz.

4. $T_J = 25$ °C, power supplies at nominal voltage.

5. Per bank. V_{CCIO} = 2.5 V. Does not include pull-up.

6. V_{CCPLL} is tied to V_{CC} internally in packages without PLLs pins.

7. V_{PP FAST}, used only for fast production programming, must be left floating or unconnected in applications.

Peak Startup Supply Current – LP Devices

Symbol	Parameter	Device	Max	Units
		iCE40LP384	7.7	mA
		iCELP640	6.4	mA
CCPEAK	Core Power Supply	iCE40LP1K	6.4	mA
		iCE40LP4K	15.7	mA
		iCE40LP8K	15.7	mA
		iCE40LP1K	1.5	mA
1, 2, 4	PLL Power Supply	iCELP640	1.5	mA
CCPLLPEAK ^{1, 2, 4}		iCE40LP4K	8.0	mA
		iCE40LP8K	8.0	mA
		iCE40LP384	3.0	mA
		iCELP640	7.7	mA
I _{PP_2V5PEAK}	NVCM Power Supply	iCE40LP1K	7.7	mA
		iCE40LP4K	4.2	mA
		iCE40LP8K	4.2	mA
		iCE40LP384	5.7	mA
IPP_FASTPEAK ³	NVCM Programming Supply	iCELP640	8.1	mA
		iCE40LP1K	8.1	mA
		iCE40LP384	8.4	mA
		iCELP640	3.3	mA
ICCIOPEAK ⁵ , ICC_SPIPEAK	Bank Power Supply	iCE40LP1K	3.3	mA
		iCE40LP4K	8.2	mA
		iCE40LP8K	8.2	mA

1. No PLL available on the iCE40LP384 and iCE40LP640 device.

2. V_{CCPLL} is tied to V_{CC} internally in packages without PLLs pins.

3. V_{PP_FAST}, used only for fast production programming, must be left floating or unconnected in applications, except CM36 and CM49 packages MUST have the V_{PP_FAST} ball connected to V_{CCIO_0} ball externally.

4. While no PLL is available in the iCE40-LP640 the I_{CCPLLPEAK} is additive to I_{CCPEAK}.

5. iCE40LP384 requires V_{CC} to be greater than 0.7 V when V_{CCIO} and V_{CC_SPI} are above GND.



Peak Startup Supply Current – HX Devices

Symbol	Parameter	Device	Max	Units
		iCE40HX1K	6.9	mA
ICCPEAK	Core Power Supply	iCE40HX4K	22.3	mA
		iCE40HX8K	6.9 22.3 22.3 1.8 6.4 6.4 4.1 4.1 6.8	mA
		iCE40HX1K	1.8	mA
I _{CCPLLPEAK} ¹	PLL Power Supply	iCE40HX4K	6.4	mA
		iCE40HX8K	6.4	mA
		iCE40HX1K	2.8	mA
I _{PP_2V5PEAK}	NVCM Power Supply	iCE40HX4K	4.1	mA
		iCE40HX8K	4.1	mA
ICCIOPEAK, ICC_SPIPEAK		iCE40HX1K	6.8	mA
	Bank Power Supply	iCE40HX4K	6.8	mA
		iCE40HX8K	6.8	mA

1. V_{CCPLL} is tied to V_{CC} internally in packages without PLLs pins.

sysIO Recommended Operating Conditions

	V _{CCIO} (V)				
Standard	Min.	Тур.	Max.		
LVCMOS 3.3	3.14	3.3	3.46		
LVCMOS 2.5	2.37	2.5	2.62		
LVCMOS 1.8	1.71	1.8	1.89		
LVDS25E ^{1, 2}	2.37	2.5	2.62		
subLVDSE ^{1, 2}	1.71	1.8	1.89		

1. Inputs on-chip. Outputs are implemented with the addition of external resistors.

2. Does not apply to Configuration Bank V_{CC_SPI}.

sysIO Single-Ended DC Electrical Characteristics

Input/	V _{IL}		V _{IH} ¹				1	
Output Standard	Min. (V)	Max. (V)	Min. (V)	Max. (V)	V _{OL} Max. (V)	V _{OH} Min. (V)	I _{OL} Max. (mA)	I _{OH} Max. (mA)
LVCMOS 3.3	-0.3	0.8	2.0	V _{CCIO} + 0.2 V	0.4	$V_{CCIO} - 0.4$	8, 16 ² , 24 ²	-8, -16 ² , -24 ²
EVOINOU 0.0	0.0	0.0	2.0	V CCIO + 0.2 V	0.2	$V_{CCIO} - 0.2$	0.1	-0.1
LVCMOS 2.5	-0.3	0.7	1.7	V _{CCIO} + 0.2 V	0.4	$V_{CCIO} - 0.4$	6, 12 ² , 18 ²	-6, -12 ² , -18 ²
2.0	0.0	0.7	1.7	V CCIO + 0.2 V	0.2	$V_{CCIO} - 0.2$	0.1	-0.1
LVCMOS 1.8	-0.3	0.35V _{CCIO}	0.65V _{CCIO}		0.4	$V_{CCIO} - 0.4$	4, 8 ² , 12 ²	-4, -8 ² , -12 ²
	-0.5	0.33 A CCIO	0.03 A CCIO	V _{CCIO} + 0.2 V	0.2	$V_{CCIO} - 0.2$	0.1	-0.1

1. Some products are clamped to a diode when V_{IN} is larger than $V_{\text{CCIO.}}$

2. Only for High Drive LED outputs.



Typical Building Block Function Performance – LP Devices^{1, 2}

Pin-to-Pin Performance (LVCMOS25)

Function	Timing	Units
Basic Functions		
16-bit decoder	11.0	ns
4:1 MUX	12.0	ns
16:1 MUX	13.0	ns

Register-to-Register Performance

Function	Timing	Units
Basic Functions	· · ·	
16:1 MUX	190	MHz
16-bit adder	160	MHz
16-bit counter	175	MHz
64-bit counter	65	MHz
Embedded Memory Functions		-
256x16 Pseudo-Dual Port RAM	240	MHz

1. The above timing numbers are generated using the iCECube2 design tool. Exact performance may vary with device and tool version. The tool uses internal parameters that have been characterized but are not tested on every device.

2. Using a V_{CC} of 1.14 V at Junction Temp 85 °C.

Typical Building Block Function Performance – HX Devices^{1, 2}

Pin-to-Pin Performance (LVCMOS25)

Function	Timing	Units
Basic Functions		
16-bit decoder	10.0	ns
4:1 MUX	9.0	ns
16:1 MUX	9.5	ns

Register-to-Register Performance

Function	Timing	Units
Basic Functions		•
16:1 MUX	305	MHz
16-bit adder	220	MHz
16-bit counter	255	MHz
64-bit counter	105	MHz
Embedded Memory Functions		•
256x16 Pseudo-Dual Port RAM	403	MHz

1. The above timing numbers are generated using the iCECube2 design tool. Exact performance may vary with device and tool version. The tool uses internal parameters that have been characterized but are not tested on every device.

2. Using a V_{CC} of 1.14 V at Junction Temp 85 °C.



Over Recommended Commercial Operating Conditions - HX Devices^{1, 2, 3, 4, 5}

Buffer Type	Description	Timing	Units
Input Adjusters	I		
LVDS25	LVDS, $V_{CCIO} = 2.5 V$	0.13	ns
subLVDS	subLVDS, V _{CCIO} = 1.8 V	1.03	ns
LVCMOS33	LVCMOS, V _{CCIO} = 3.3 V	0.16	ns
LVCMOS25	LVCMOS, V _{CCIO} = 2.5 V	0.00	ns
LVCMOS18	LVCMOS, V _{CCIO} = 1.8 V	0.23	ns
Output Adjusters	· · ·		
LVDS25E	LVDS, Emulated, V _{CCIO} = 2.5 V	0.00	ns
subLVDSE	subLVDS, Emulated, V _{CCIO} = 1.8 V	1.76	ns
LVCMOS33	LVCMOS, V _{CCIO} = 3.3 V	0.17	ns
LVCMOS25	LVCMOS, V _{CCIO} = 2.5 V	0.00	ns
LVCMOS18	LVCMOS, V _{CCIO} = 1.8 V	1.76	ns

1. Timing adders are relative to LVCMOS25 and characterized but not tested on every device.

2. LVCMOS timing measured with the load specified in Switching Test Condition table.

3. All other standards tested according to the appropriate specifications.

4. Commercial timing numbers are shown.

5. Not all I/O standards are supported for all banks. See the Architecture section of this data sheet for details.



iCE40 External Switching Characteristics – LP Devices ^{1, 2}

Over Recommended Operating Conditions

Parameter	Description	Device	Min.	Max.	Units
Clocks					
Global Clocks					
f _{MAX_GBUF}	Frequency for Global Buffer Clock network	All iCE40LP devices	—	275	MHz
t _{W_GBUF}	Clock Pulse Width for Global Buffer	All iCE40LP devices	0.92		ns
		iCE40LP384	-	370	ps
		iCE40LP640	-	230	ps
t _{SKEW_GBUF}	Global Buffer Clock Skew Within a Device	iCE40LP1K	_	230	ps
		iCE40LP4K	-	340	ps
		iCE40LP8K	-	340	ps
Pin-LUT-Pin Propa	agation Delay			1	1
t _{PD} Best case propagation delay through one LUT-4		All iCE40LP devices	—	9.36	ns
General I/O Pin Pa	rameters (Using Global Buffer Clock withou	ut PLL) ³			
		iCE40LP384	—	300	ps
		iCE40LP640	— —	200	ps
t _{skew_io} D	Data bus skew across a bank of IOs	iCE40LP1K		200	ps
		iCE40LP4K		280	ps
		iCE40LP8K		280	ps
		iCE40LP384		6.33	ns
		iCE40LP640		5.91	ns
t _{CO}	Clock to Output - PIO Output Register	iCE40LP1K		5.91	ns
		iCE40LP4K		6.58	ns
		iCE40LP8K		6.58	ns
		iCE40LP384	-0.08		ns
		iCE40LP640	-0.33		ns
t _{SU}	Clock to Data Setup - PIO Input Register	iCE40LP1K	-0.33		ns
		iCE40LP4K	-0.63		ns
		iCE40LP8K	-0.63		ns
		iCE40LP384	1.99		ns
		iCE40LP640	2.81		ns
t _H	Clock to Data Hold - PIO Input Register	iCE40LP1K	2.81		ns
		iCE40LP4K	3.48		ns
		iCE40LP8K	3.48		ns
General I/O Pin Pa	Irameters (Using Global Buffer Clock with P	LL) ³	I	I	1
		iCE40LP1K		2.20	ns
t _{COPLL}	Clock to Output - PIO Output Register	iCE40LP4K		2.30	ns
		iCE40LP8K		2.30	ns
		iCE40LP1K	5.23		ns
t _{SUPLL}	Clock to Data Setup - PIO Input Register	iCE40LP4K	6.13		ns
		iCE40LP8K	6.13		ns



iCE40 External Switching Characteristics – LP Devices (Continued)^{1, 2}

Over Recommended Operating Conditions

Parameter	Description	Device	Min.	Max.	Units
		iCE40LP1K	-0.90	_	ns
t _{HPLL}		iCE40LP4K	-0.80	_	ns
		iCE40LP8K	-0.80		ns

1. Exact performance may vary with device and design implementation. Commercial timing numbers are shown at 85 °C and 1.14 V. Other operating conditions can be extracted from the iCECube2 software.

2. General I/O timing numbers based on LVCMOS 2.5, 0pf load.

3. Supported on devices with a PLL.



sysCONFIG Port Timing Specifications¹ (Continued)

Symbol	Parameter		Min.	Тур.	Max.	Units
		iCE40LP384 - Low Frequency (Default)	600	_	—	us
		iCE40LP384 - Medium Frequency	600	_	—	us
		iCE40LP384 - High Frequency	600	_	—	us
		iCE40LP640, iCE40LP/HX1K - Low Frequency (Default)	800	_	_	us
		iCE40LP640, iCE40LP/HX1K - Medium Frequency	800	_	_	us
		iCE40LP640, iCE40LP/HX1K - High Frequency	800		_	us
	CRESET_B high to first MCLK	iCE40LP/HX1K-Low Frequency (Default)	800	_	—	us
^I MCLK	edge	iCE40LP/HX1K - Medium Frequency	800	_	—	us
		iCE40LP/HX1K - High Frequency	800	_	—	us
		iCE40LP/HX4K - Low Frequency (Default)	1200		—	us
		iCE40LP/HX4K - Medium Frequency	1200	_	—	us
		iCE40LP/HX4K - high frequency	1200	_	—	US
		iCE40LP/HX8K - Low Frequency (Default)	1200	_	—	us
		iCE40LP/HX8K - Medium Frequency	1200		—	us
		iCE40LP/HX8K - High Frequency	1200			us

Does not apply for NVCM.
Supported only with 1.2 V V_{CC} and at 25 °C.
Extended range f_{MAX} Write operations support up to 53 MHz only with 1.2 V V_{CC} and at 25 °C.



Switching Test Conditions

Figure 3-3 shows the output test load used for AC testing. The specific values for resistance, capacitance, voltage, and other test conditions are shown in Table 3-3.

Figure 3-3. Output Test Load, LVCMOS Standards

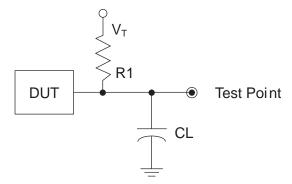


Table 3-3. Test Fixture Required Components, Non-Terminated Interfaces

Test Condition	R ₁	CL	Timing Reference	V _T		
			LVCMOS 3.3 = 1.5 V	—		
LVCMOS settings (L -> H, H -> L)	×	0 pF	LVCMOS 2.5 = $V_{CCIO}/2$	—		
			LVCMOS 1.8 = $V_{CCIO}/2$	—		
LVCMOS 3.3 (Z -> H)			1.5	V _{OL}		
LVCMOS 3.3 (Z -> L)					1.5	V _{OH}
Other LVCMOS (Z -> H)	188	0 pF	V _{CCIO} /2	V _{OL}		
Other LVCMOS (Z -> L)	100	0 pr	V _{CCIO} /2	V _{OH}		
LVCMOS (H -> Z)			V _{OH} - 0.15	V _{OL}		
LVCMOS (L -> Z)			V _{OL} - 0.15	V _{OH}		

Note: Output test conditions for all other interfaces are determined by the respective standards.



Signal Descriptions (Continued)

Signal Name	I/O	Descriptions
VPP_FAST		Optional fast NVCM programming supply. V _{PP_FAST} , used only for fast production programming, must be left floating or unconnected in applications, except CM36 and CM49 packages MUST have the V _{PP_FAST} ball connected to V _{CCIO_0} ball externally.
VPP_2V5	—	VPP_2V5 NVCM programming and operating supply



Pin Information Summary (Continued)

	iCE40LP4K			iCE40LP8K			iCE40HX1K		
	CM81	CM121	CM225	CM81	CM121	CM225	VQ100	CB132	TQ144
General Purpose I/O per	r Bank								
Bank 0	17	23	46	17	23	46	19	24	23
Bank 1	15	21	42	15	21	42	19	25	25
Bank 2	9	19	40	9	19	40	12	20	20
Bank 3	18	26	46	18	26	46	18	22	24
Configuration	4	4	4	4	4	4	4	4	4
Total General Purpose Single Ended I/O	63	93	178	63	93	178	72	95	96
High Current Outputs p	er Bank	•	•		•	•	•	•	•
Bank 0	0	0	0	0	0	0	0	0	0
Bank 1	0	0	0	0	0	0	0	0	0
Bank 2	0	0	0	0	0	0	0	0	0
Bank 3	0	0	0	0	0	0	0	0	0
Total Differential Inputs	0	0	0	0	0	0	0	0	0
Differential Inputs per B	ank								
Bank 0	0	0	0	0	0	0	0	0	0
Bank 1	0	0	0	0	0	0	0	0	0
Bank 2	0	0	0	0	0	0	0	0	0
Bank 3	9	13	23	9	13	23	9	11	12
Total Differential Inputs	9	13	23	9	13	23	9	11	12
Dedicated Inputs per Ba	ank								
Bank 0	0	0	0	0	0	0	0	0	0
Bank 1	0	0	1	0	0	1	0	1	1
Bank 2	2	2	2	2	2	2	2	2	2
Bank 3	0	0	0	0	0	0	0	0	0
Configuration	0	0	0	0	0	0	0	0	0
Total Dedicated Inputs	2	2	3	2	2	3	2	3	3
Vccio Pins									
Bank 0	1	1	3	1	1	3	2	2	2
Bank 1	1	1	3	1	1	3	2	2	2
Bank 2	1	1	3	1	1	3	2	2	2
Bank 3	1	2	4	1	2	4	3	3	2
VCC	3	4	8	3	4	8	4	5	4
VCC_SPI	1	1	1	1	1	1	1	1	1
VPP_2V5	1	1	1	1	1	1	1	1	1
VPP_FAST ¹	1	1	1	1	1	1	1	1	1
VCCPLL	1	2	2	1	2	2	0	1	1
GND	5	12	18	5	12	18	10	14	10
NC	0	0	0	0	0	0	0	2	19
Total Count of Bonded Pins	81	121	225	81	121	225	100	132	144

1. V_{PP_FAST}, used only for fast production programming, must be left floating or unconnected in applications.



Pin Information Summary (Continued)

		iCE40HX4K		iCE40HX8K				
	BG121	CB132	TQ144	BG121	CB132	CM225	CT256	
General Purpose I/O per Bank								
Bank 0	23	24	27	23	24	46	52	
Bank 1	21	25	29	21	25	42	52	
Bank 2	19	18	19	19	18	40	46	
Bank 3	26	24	28	26	24	46	52	
Configuration	4	4	4	4	4	4	4	
Total General Purpose Single Ended I/O	93	95	107	93	95	178	206	
High Current Outputs per Bank		•	•		•			
Bank 0	0	0	0	0	0	0	0	
Bank 1	0	0	0	0	0	0	0	
Bank 2	0	0	0	0	0	0	0	
Bank 3	0	0	0	0	0	0	0	
Total Differential Inputs	0	0	0	0	0	0	0	
Differential Inputs per Bank	•	•			•	•		
Bank 0	0	0	0	0	0	0	0	
Bank 1	0	0	0	0	0	0	0	
Bank 2	0	0	0	0	0	0	0	
Bank 3	13	12	14	13	12	23	26	
Total Differential Inputs	13	12	14	13	12	23	26	
Dedicated Inputs per Bank		•	•		•			
Bank 0	0	0	0	0	0	0	0	
Bank 1	0	1	1	0	1	1	1	
Bank 2	2	2	2	2	2	2	2	
Bank 3	0	0	0	0	0	0	0	
Configuration	0	0	0	0	0	0	0	
Total Dedicated Inputs	2	3	3	2	3	3	3	
Vccio Pins	•		•	•	•		•	
Bank 0	1	2	2	1	2	3	4	
Bank 1	1	2	2	1	2	3	4	
Bank 2	1	2	2	1	2	3	4	
Bank 3	2	3	2	2	3	4	4	
VCC	4	5	4	4	5	8	6	
VCC_SPI	1	1	1	1	1	1	1	
VPP_2V5	1	1	1	1	1	1	1	
VPP_FAST ¹	1	1	1	1	1	1	1	
VCCPLL	2	2	2	2	2	2	2	
GND	12	15	11	12	15	18	20	
NC	0	0	6	0	0	0	0	
Total Count of Bonded Pins	121	132	144	121	132	225	256	

1. V_{PP_FAST}, used only for fast production programming, must be left floating or unconnected in applications.



Ultra Low Power Industrial Grade Devices, Halogen Free (RoHS) Packaging

Part Number	LUTs	Supply Voltage	Package	Leads	Temp.
ICE40LP384-CM36	384	1.2 V	Halogen-Free ucBGA	36	IND
ICE40LP384-CM36TR	384	1.2 V	Halogen-Free ucBGA	36	IND
ICE40LP384-CM36TR1K	384	1.2 V	Halogen-Free ucBGA	36	IND
ICE40LP384-CM49	384	1.2 V	Halogen-Free ucBGA	49	IND
ICE40LP384-CM49TR	384	1.2 V	Halogen-Free ucBGA	49	IND
ICE40LP384-CM49TR1K	384	1.2 V	Halogen-Free ucBGA	49	IND
ICE40LP384-SG32	384	1.2 V	Halogen-Free QFN	32	IND
ICE40LP384-SG32TR	384	1.2 V	Halogen-Free QFN	32	IND
ICE40LP384-SG32TR1K	384	1.2 V	Halogen-Free QFN	32	IND
ICE40LP640-SWG16TR	640	1.2 V	Halogen-Free WLCSP	16	IND
ICE40LP640-SWG16TR50	640	1.2 V	Halogen-Free WLCSP	16	IND
ICE40LP640-SWG16TR1K	640	1.2 V	Halogen-Free WLCSP	16	IND
ICE40LP1K-SWG16TR	1280	1.2 V	Halogen-Free WLCSP	16	IND
ICE40LP1K-SWG16TR50	1280	1.2 V	Halogen-Free WLCSP	16	IND
ICE40LP1K-SWG16TR1K	1280	1.2 V	Halogen-Free WLCSP	16	IND
ICE40LP1K-CM36	1280	1.2 V	Halogen-Free ucBGA	36	IND
ICE40LP1K-CM36TR	1280	1.2 V	Halogen-Free ucBGA	36	IND
ICE40LP1K-CM36TR1K	1280	1.2 V	Halogen-Free ucBGA	36	IND
ICE40LP1K-CM49	1280	1.2 V	Halogen-Free ucBGA	49	IND
ICE40LP1K-CM49TR	1280	1.2 V	Halogen-Free ucBGA	49	IND
ICE40LP1K-CM49TR1K	1280	1.2 V	Halogen-Free ucBGA	49	IND
ICE40LP1K-CM81	1280	1.2 V	Halogen-Free ucBGA	81	IND
ICE40LP1K-CM81TR	1280	1.2 V	Halogen-Free ucBGA	81	IND
ICE40LP1K-CM81TR1K	1280	1.2 V	Halogen-Free ucBGA	81	IND
ICE40LP1K-CB81	1280	1.2 V	Halogen-Free csBGA	81	IND
ICE40LP1K-CB81TR	1280	1.2 V	Halogen-Free csBGA	81	IND
ICE40LP1K-CB81TR1K	1280	1.2 V	Halogen-Free csBGA	81	IND
ICE40LP1K-CM121	1280	1.2 V	Halogen-Free ucBGA	121	IND
ICE40LP1K-CM121TR	1280	1.2 V	Halogen-Free ucBGA	121	IND
ICE40LP1K-CM121TR1K	1280	1.2 V	Halogen-Free ucBGA	121	IND
ICE40LP1K-CB121	1280	1.2 V	Halogen-Free csBGA	121	IND
ICE40LP1K-QN84	1280	1.2 V	Halogen-Free QFN	84	IND
ICE40LP4K-CM81	3520	1.2 V	Halogen-Free ucBGA	81	IND
ICE40LP4K-CM81TR	3520	1.2 V	Halogen-Free ucBGA	81	IND
ICE40LP4K-CM81TR1K	3520	1.2 V	Halogen-Free ucBGA	81	IND
ICE40LP4K-CM121	3520	1.2 V	Halogen-Free ucBGA	121	IND
ICE40LP4K-CM121TR	3520	1.2 V	Halogen-Free ucBGA	121	IND
ICE40LP4K-CM121TR1K	3520	1.2 V	Halogen-Free ucBGA	121	IND
ICE40LP4K-CM225	3520	1.2 V	Halogen-Free ucBGA	225	IND
ICE40LP8K-CM81	7680	1.2 V	Halogen-Free ucBGA	81	IND
ICE40LP8K-CM81TR	7680	1.2 V	Halogen-Free ucBGA	81	IND
ICE40LP8K-CM81TR1K	7680	1.2 V	Halogen-Free ucBGA	81	IND
ICE40LP8K-CM121	7680	1.2 V	Halogen-Free ucBGA	121	IND
ICE40LP8K-CM121TR	7680	1.2 V	Halogen-Free ucBGA	121	IND



iCE40 LP/HX Family Data Sheet Supplemental Information

March 2017

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For Further Information

A variety of technical notes for the iCE40 family are available on the Lattice web site.

- TN1248, iCE40 Programming and Configuration
- TN1250, Memory Usage Guide for iCE40 Devices
- TN1251, iCE40 sysCLOCK PLL Design and Usage Guide
- TN1252, iCE40 Hardware Checklist
- TN1253, Using Differential I/O (LVDS, Sub-LVDS) in iCE40 Devices
- TN1074, PCB Layout Recommendations for BGA Packages
- iCE40 Pinout Files
- Thermal Management document
- Lattice design tools
- IBIS
- Package Diagrams Data Sheet
- Schematic Symbols

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